

**Infrared Emitting Diode**

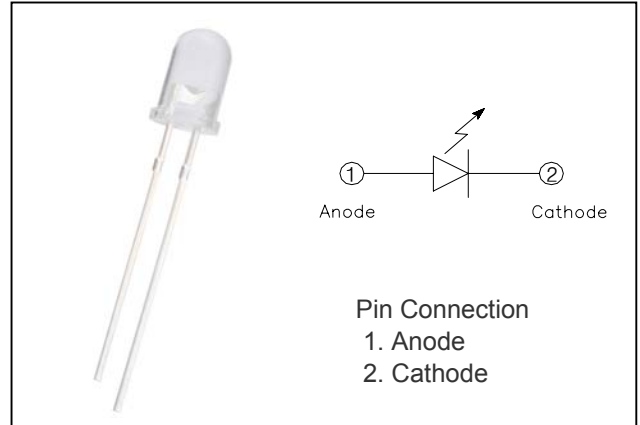
**KEL5002A**

**Description**

The KEL5002A is GaAlAs infrared emitting diode that is designed for high power, low forward voltage. This device is optimized for speed and efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T13/4 package.

**Features**

- 940nm wavelength
- Low forward voltage
- High power and high reliability
- Available for pulse operating



**Applications**

- IR Audio and Telephone
- IR communication
- Optical Switch
- Available for wireless digital data transmission

**Absolute Maximum Ratings** [T<sub>A</sub> = 25°C ]

Parameter	Symbol	Min.	Max.	Max.
Reverse Voltage	V <sub>R</sub>	-	5	V
Forward Current	I <sub>F</sub>	-	100	mA
Power Dissipation	P <sub>D</sub>	-	170	mW
Pulse Forward Current*1	I <sub>FP</sub>	-	1.0	A
Operating Temperature	T <sub>opr</sub>	-30	85	°C
Storage Temperature	T <sub>stg</sub>	-30	100	°C
Soldering Temperature*2	T <sub>sol</sub>	-	260	°C

\*1 : Pulse Width : Tw ≤ 100μs, Periode : T = 10ms

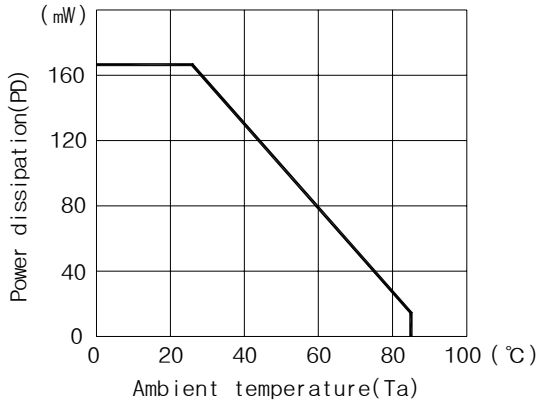
\*2 : MAX 5s

The contents of this data sheet are subject to change without advance notice for the purpose of improvement. When using this product, would you please refer to the latest specifications.

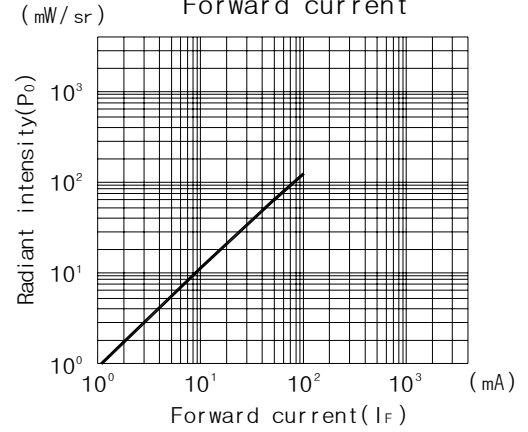
# KEL5002A

## Rating and Characteristic Curves

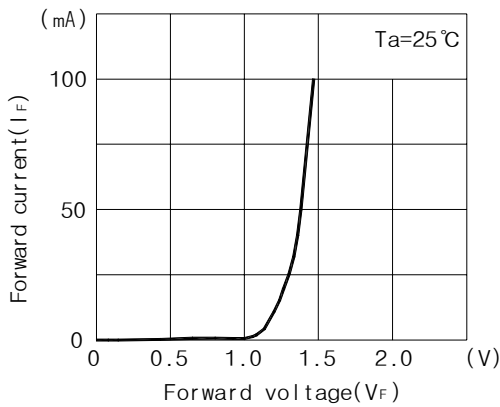
Power dissipation Vs. Ambient temperature



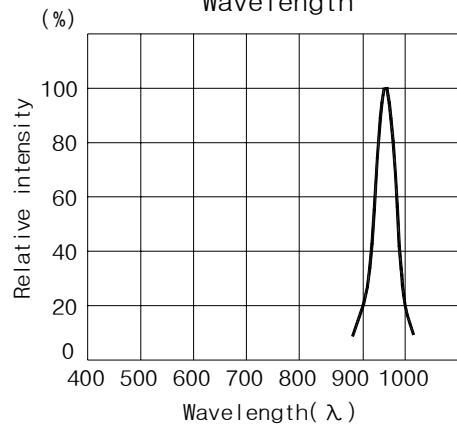
Relative intensity Vs. Forward current



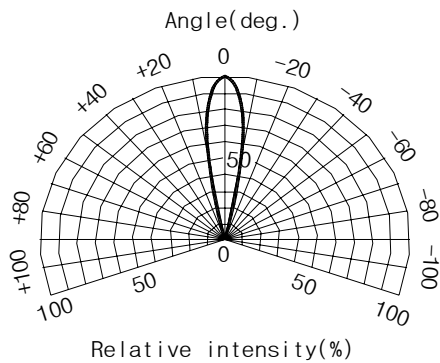
Forward current Vs. Forward voltage



Relative intensity Vs. Wavelength



Radiant Pattern



The contents of this data sheet are subject to change without advance notice for the purpose of improvement.  
When using this product, would you please refer to the latest specifications.

# KEL5002A

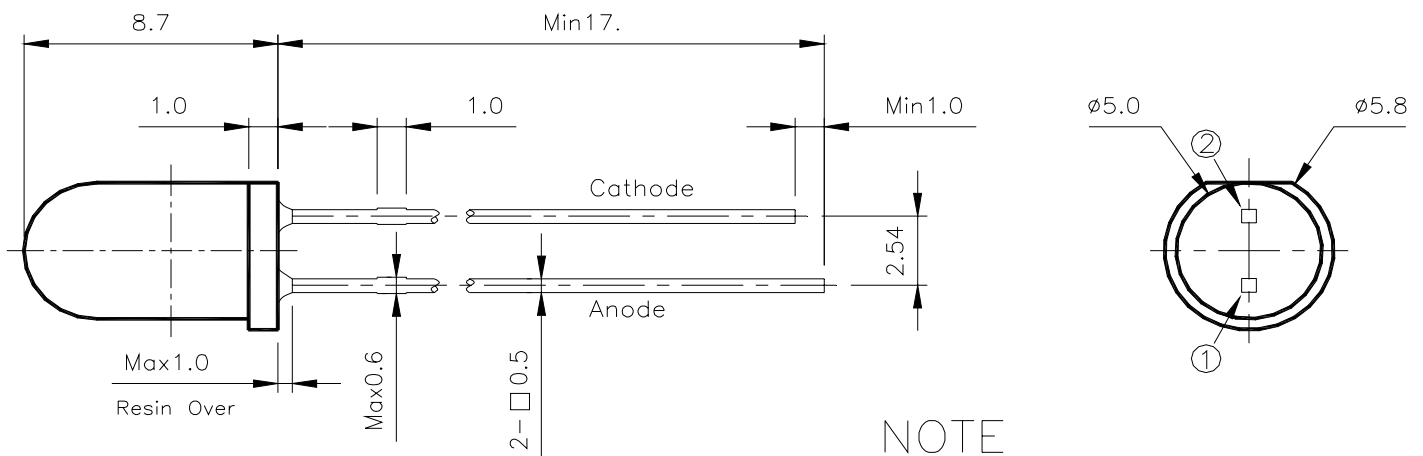
## Electrical Characteristics

[T<sub>A</sub> = 25°C]

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =50mA	-	1.4	1.7	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =5V	-	-	10	μA
Radiant Intensity	I <sub>e</sub>	I <sub>F</sub> =50mA	30	60	-	mW/ sr
Peak Emission Wavelength	λ <sub>p</sub>	I <sub>F</sub> =50mA	-	940	-	nm
Spectral Bandwidth 50%	Δλ	I <sub>F</sub> =50mA	-	45	-	nm
Half Angle	Δθ	I <sub>F</sub> =50mA	-	±10		deg.

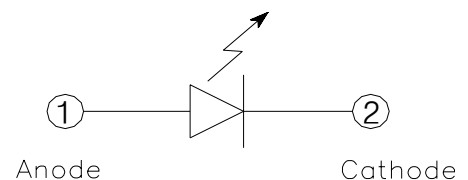
## Package Outline Dimensions

(Unit : mm)



## NOTE

1. GENERAL TOLERANCE : ±0.2
2. THICKNESS : 0.5mm
3. PIN CONFIGURATION



The contents of this data sheet are subject to change without advance notice for the purpose of improvement.  
When using this product, would you please refer to the latest specifications.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [knowledge-on](#) manufacturer:*

Other Similar products are found below :

[OPE5685](#)